

Plastic Infrared Emitting Diode

OP265, OP266 Series

(A, B, D, W)



Features:

- T-1 (3 mm) package style
- Choice of narrow or wide irradiance pattern
- Choice of dome or flat lens
- Mechanically and spectrally matched to other OPTEK devices
- Higher power output than GaAs at equivalent drive currents
- 890 nm diodes



Description:

Each device in the **OP265** and **OP266** series is a high intensity gallium arsenide infrared emitting diode (GaAIAs) that is molded in an IR transmissive clear epoxy package with either a dome or flat lens. Devices feature narrow and wide irradiance patterns and a variety of electrical characteristics. The small T-1 package style makes these devices ideal for space-limited applications.

OP265 devices conform to the OP505 and OP535 series devices. OP266 devices conform to OP506 series devices.

Please refer to Application Bulletins 208 and 210 for additional design information and reliability (degradation) data.

Applications:

- Space-limited applications
- Applications requiring coupling efficiency
- Battery-operated or voltage-limited applications

Ordering Information					
Part Number	LED Peak Wavelength	Output Power (mW/cm ²) Min / Max	I _F (mA) Typ / Max	Total Beam Angle	Lead Length
OP265A	890 nm	2.70 / NA	20 / 50	18°	See page 2
OP265B		1.65 / 4.70			
OP265D		0.54 / NA			
OP265W		1.00 / NA		90°	
OP266A		2.70 / NA			
OP266B		1.65 / 4.70		18°	
OP266D		0.54 / NA			
OP266W		1.00 / NA		90°	



RoHS

General Note
TT Electronics reserves the right to make changes in product specification without notice or liability. All information is subject to TT Electronics' own data and is considered accurate at time of going to print.

OPTEK Technology, Inc.
1645 Wallace Drive, Carrollton, TX 75006 | Ph: +1 972 323 2200
www.optekinc.com | www.ttelectronics.com

Plastic Infrared Emitting Diode

OP265, OP266 Series

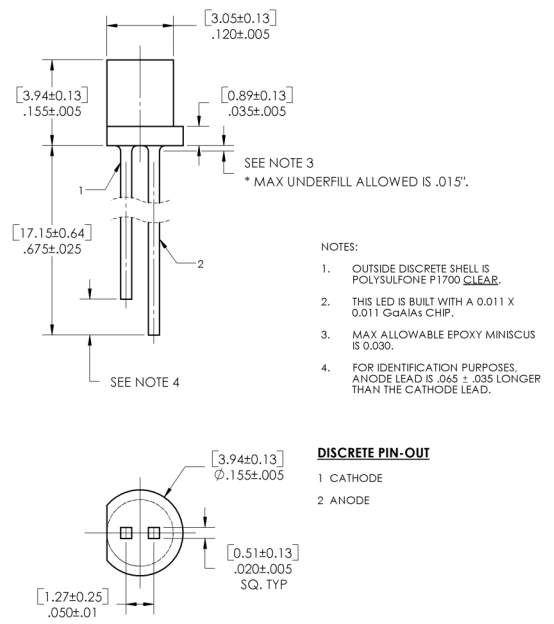
(A, B, D, W)



OP265 (A, B, D)



OP265W

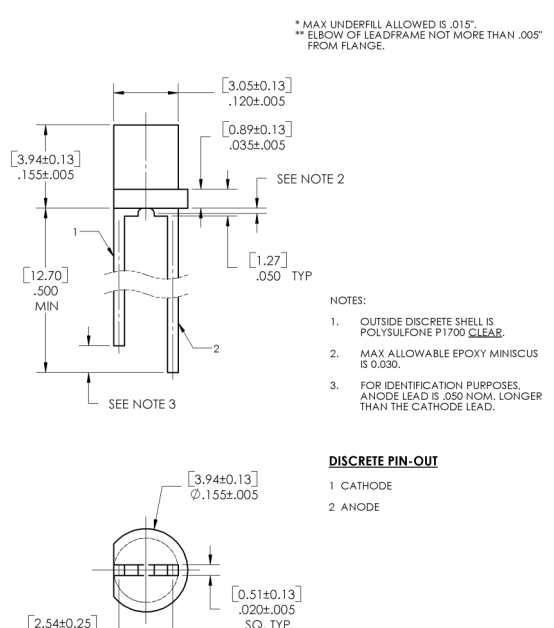


DIMENSIONS ARE IN: [MILLIMETERS]
[INCHES]

OP266 (A, B, D)



OP266W



Pin #	LED
1	Cathode
2	Anode

CONTAINS POLYSULFONE

To avoid stress cracking, we suggest using ND Industries' **Vibra-Tite** for thread-locking. **Vibra-Tite** evaporates fast without causing structural failure in OPTEK's molded plastics.

General Note

TT Electronics reserves the right to make changes in product specification without notice or liability. All information is subject to TT Electronics' own data and is considered accurate at time of going to print.

OPTEK Technology, Inc.
1645 Wallace Drive, Carrollton, TX 75006 | Ph: +1 972 323 2200
www.optekinc.com | www.ttelectronics.com

Plastic Infrared Emitting Diode

OP265, OP266 Series

(A, B, D, W)



Electrical Specifications

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)	
Storage and Operating Temperature Range	-40°C to $+100^\circ\text{C}$
Reverse Voltage	2.0 V
Continuous Forward Current	50 mA
Peak Forward Current (1 μs pulse width, 300 pps)	3.0 A
Lead Soldering Temperature [1/16 inch (1.6 mm) from case for 5 seconds with soldering iron]	260°C
Power Dissipation	$100\text{ mW}^{(1)}$

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)							
SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS	
Input Diode							
$E_{E(APT)}$	Apertured Radiant Incidence						
	OP265A, OP266A	2.70	-	-	mW/cm ²	$I_F = 20\text{ mA}^{(2)}$	
	OP265B, OP266B	1.65	-	4.70			
OP265D, OP266D	0.54	-	-				
P_O	Radiant Power Output				mW	$I_F = 20\text{ mA}$	
	OP265, OP266 (A, B, D) OP265W, OP266W	- 1.00	- -	- -			
V_F	Forward Voltage	-	-	1.80	V	$I_F = 20\text{ mA}$	
I_R	Reverse Current	-	-	100	μA	$V_R = 2\text{ V}$	
λ_P	Wavelength at Peak Emission	-	890	-	nm	$I_F = 10\text{ mA}$	
B	Spectral Bandwidth between Half Power Points	-	80	-	nm	$I_F = 10\text{ mA}$	
$\Delta\lambda_P/\Delta T$	Spectral Shift with Temperature	OP265,	-	± 0.30	-	nm/ $^\circ\text{C}$	$I_F = \text{Constant}$
		OP266 (A, B, D) OP265W, OP266W	-	± 0.18	-		
θ_{HP}	Emission Angle at Half Power Points	OP265,	-	18	-	Degree	$I_F = 20\text{ mA}$
		OP266 (A, B, D) OP265W, OP266W	-	90	-		
t_r	Output Rise Time	-	500	-	ns	$I_{F(PK)}=100\text{ mA}$, PW=10 μs , D.C.=10.0%	
t_f	Output Fall Time	-	250	-	ns	$I_{F(PK)}=100\text{ mA}$, PW=10 μs , D.C.=10.0%	

Notes:

- Derate linearly 1.33 mW/ $^\circ\text{C}$ above 25°C
- $E_{E(APT)}$ is a measurement of the average apertured radiant incidence upon a sensing area 0.081" (2.06 mm) in diameter, perpendicular to and centered on the mechanical axis of the lens, and 0.590" (14.99 mm) from the measurement surface. $E_{E(APT)}$ is not necessarily uniform within the measured areas.



General Note

TT Electronics reserves the right to make changes in product specification without notice or liability. All information is subject to TT Electronics' own data and is considered accurate at time of going to print.

OPTEK Technology, Inc.
1645 Wallace Drive, Carrollton, TX 75006 | Ph: +1 972 323 2200
www.optekinc.com | www.ttelectronics.com

Plastic Infrared Emitting Diode

OP265, OP266 Series

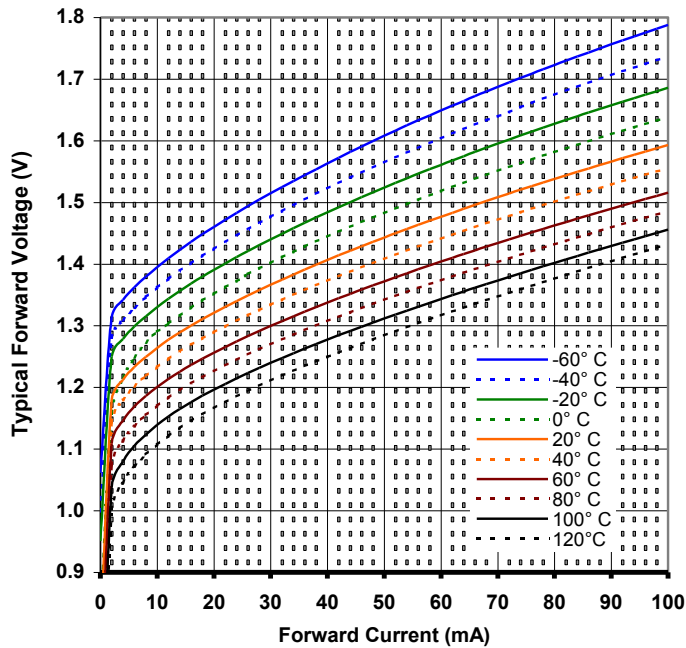
(A, B, D, W)



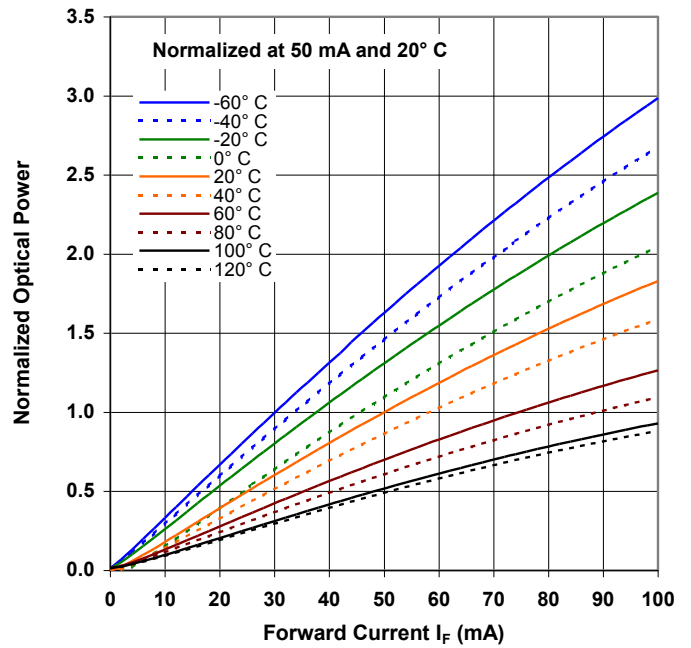
Performance

OP265, OP266 (A, B, D, W)

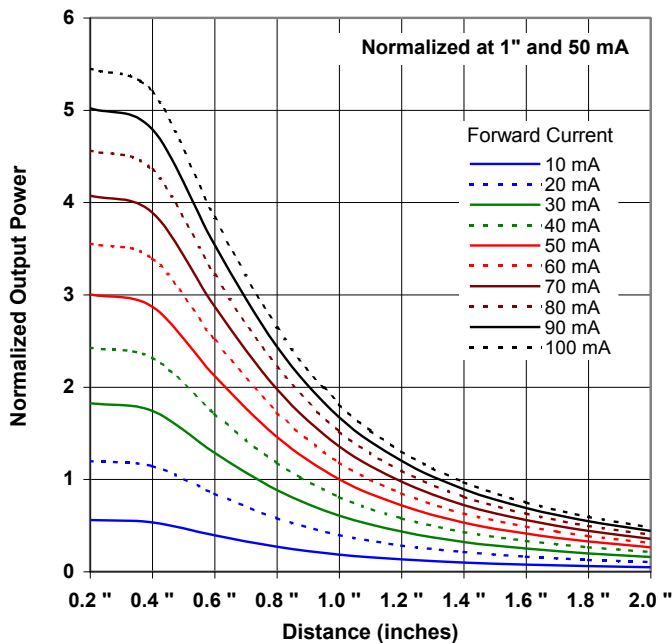
Forward Voltage vs Forward Current vs Temperature



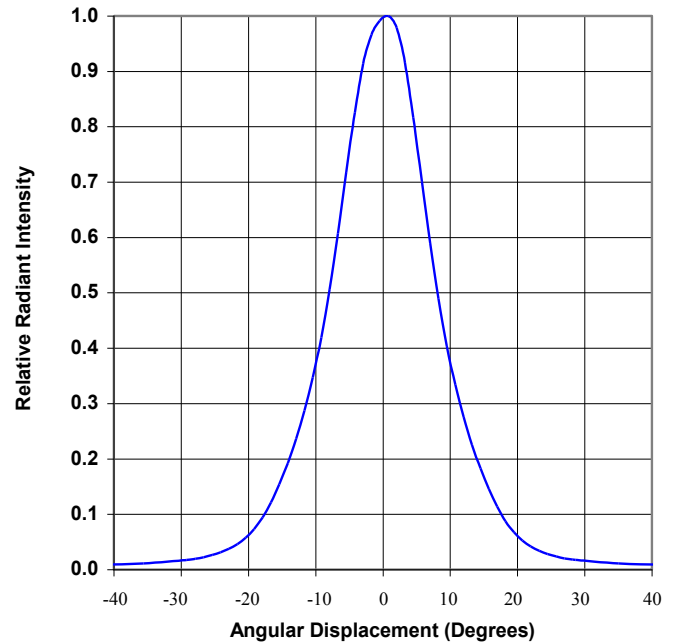
Optical Power vs I_F vs Temperature



Distance vs Output Power vs Forward Current



Relative Radiant Intensity vs. Angular Displacement



General Note

TT Electronics reserves the right to make changes in product specification without notice or liability. All information is subject to TT Electronics' own data and is considered accurate at time of going to print.

OPTEK Technology, Inc.
1645 Wallace Drive, Carrollton, TX 75006 | Ph: +1 972 323 2200
www.optekinc.com | www.ttelectronics.com

Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9